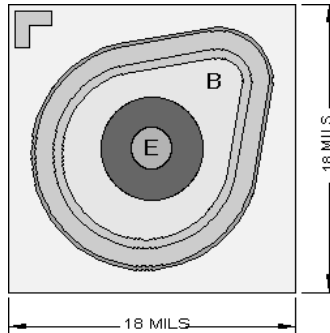


**Chip Type 2C2605**  
**Geometry 0220**  
**Polarity NPN**

**Generic Packaged Parts:**  
**2N2604, 2N2605, 2N3798,**  
**2N3799, 2N3810, 2N3811**



[Request Quotation](#)

Chip type **2C2605** by Semicoa Semiconductors provides performance similar to these devices.

**Product Summary:**

**APPLICATIONS:** Designed for high speed switching applications.

**Part Numbers:**

2N2604, [2N2605](#), 2N3789, 2N3799, [2N3810](#), [2N3811](#)

**Features:**

- High speed switching capabilities

Mechanical Specifications		
Metallization	Top	Al - 19.5 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	3.6 mils diameter
	Base	2.5 mils diameter
Die Thickness	8 mils nominal	
Chip Area	18 mils x 18 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
$T_A = 25^\circ\text{C}$				
Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 10.0 \text{ A}, I_B = 0$	60	---	V dc
$BV_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	70	---	V dc
$BV_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	6.0	---	V dc
$I_{CBO}$	$V_{CB} = 60 \text{ V}, I_E = 0$	---	10	nA
$h_{FE}$	$I_C = 500 \mu\text{A dc}, V_{CE} = 5.0 \text{ V}$	150	450	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*